



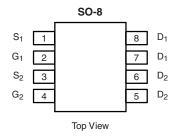
## **Dual N-Channel 30-V (D-S) MOSFET**

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	
30	0.025 at V <sub>GS</sub> = 10 V	± 6.9	
	0.035 at V <sub>GS</sub> = 4.5 V	± 5.8	

#### **FEATURES**

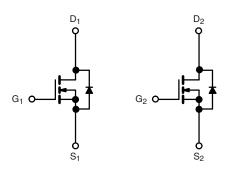
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- 100 %  $\rm R_{\rm g}$  Tested Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4920DY-T1-E3 (Lead (Pb)-free)

Si4920DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	<b>S</b> T <sub>A</sub> = 25 °C, unle	ss otherwise n	oted	
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	30	.,
Gate-Source Voltage		$V_{GS}$	± 20	V
Continuous Dusin Courset /T. 150 °CV8	T <sub>A</sub> = 25 °C	I <sub>D</sub>	± 6.9	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		± 5.5	•
Pulsed Drain Current (10 μs Pulse Width)		I <sub>DM</sub>	± 40	A
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.7	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2	10/
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	r D	1.3	─ W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	62.5	°C/W	

Notes:

a. Surface Mounted on FR4 board,  $t \le 10 \text{ s.}$ 

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SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static				1	1				
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1			V			
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V$ , $V_{GS} = \pm 20 V$			± 100	nA			
Zero Gate Voltage Drain Current	1	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1				
	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			25	μΑ			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α			
Drain-Source On-State Resistance <sup>a</sup>	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.9 A		0.020	0.025				
	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 5.8 \text{ A}$		0.026	0.035	Ω			
Forward Transconductancea	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_D = 6.9 \text{ A}$		25		S			
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 1.7 A, V <sub>GS</sub> = 0 V			1.2	V			
Dynamic <sup>b</sup>									
Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 6.9 \text{ A}$		15	23				
Total Gate Charge	Q <sub>gt</sub>			30	50	nC			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6.9 \text{ A}$		7.5					
Gate-Drain Charge	$Q_{gd}$			3.5					
Gate Resistance	$R_g$	f = 1 MHz		2	3	Ω			
Turn-On Delay Time	t <sub>d(on)</sub>			12	20				
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$		10	20	ns			
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 $\Omega$		60	90				
Fall Time	t <sub>f</sub>			15	30				
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.7 A, dI/dt = 100 A/μs		50	90				

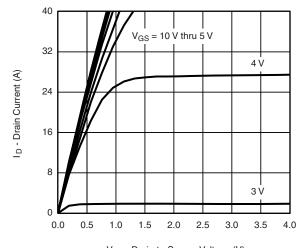
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



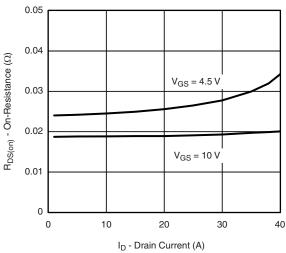


#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

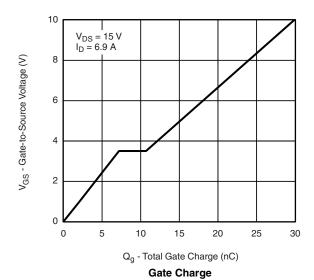


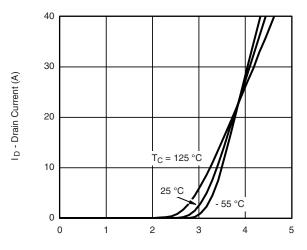
 $V_{\text{DS}}$  - Drain-to-Source Voltage (V)

#### **Output Characteristics**



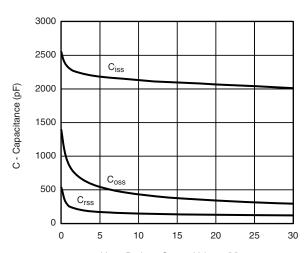
On-Resistance vs. Drain Current





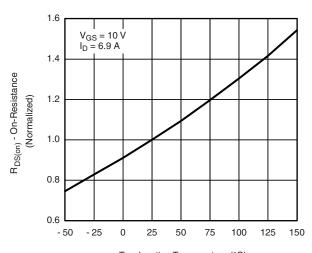
 $V_{\mbox{\footnotesize GS}}$  - Gate-to-Source Voltage (V)

#### **Transfer Characteristics**



 $V_{DS}$  - Drain-to-Source Voltage (V)

#### Capacitance

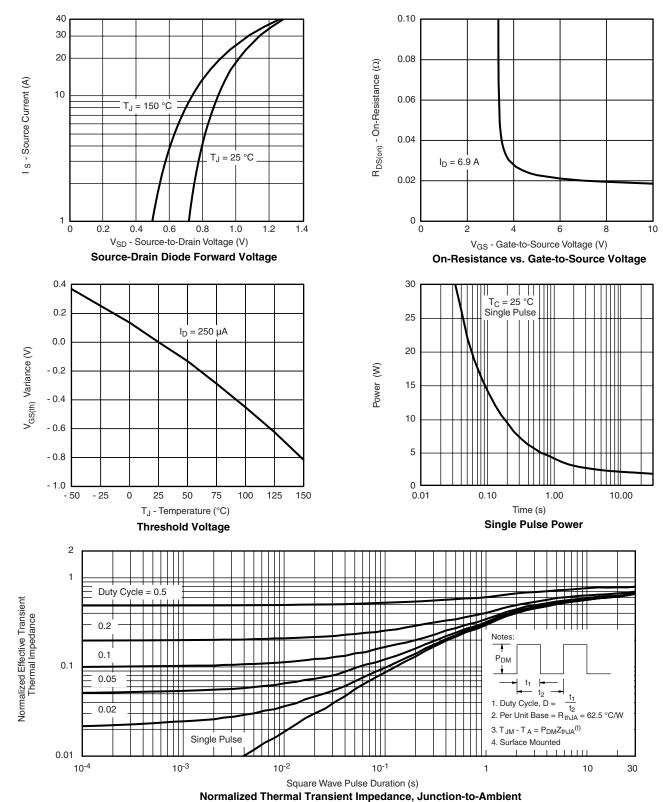


 $T_J$  - Junction T emperature (°C)

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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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